ES3A THRU ES3M

SUPER FAST SURFACE MOUNT RECTIFIERS

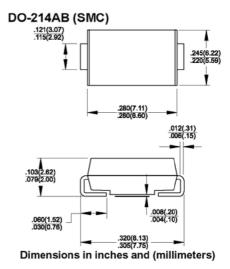
Reverse Voltage - 50 to 1000 Volts Forward Current - 3.0 Amperes

Features

- ◆ Glass passivated junction chip
- ◆ For surface mounted application
- ◆ Low profile package
- ◆ Built-in strain relief
- ◆ Ideal for automated placement
- ◆ Easy pick and place
- ◆ Superfast recovery time for high efficiency
- Superrast recovery time for nig
 Glass passivated chip junction
- ◆ High temperature soldering: 250°C/10 seconds at terminals
- Plastic material used carries Underwriters Laboratory Classification 94V-O

Mechanical Data

- ◆ Cases: Molded plastic
- ◆ Terminals: Solder plated
- ◆ Polarity: Indicated by cathode band
- ◆ Weight: 0.007 ounce, 0.21 gram



Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Parameter	Symbols	ES 3A	ES 3B	ES 3C	ES 3D	ES 3F	ES 3G	ES 3J	ES 3K	ES 3M	Units
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	150	200	300	400	600	800	1000	Volts
Maximum RMS voltage	V _{RMS}	35	70	105	140	210	280	420	560	700	Volts
Maximum DC blocking voltage	V _{DC}	50	100	150	200	300	400	600	800	1000	Volts
Maximum average forward rectified current See Fig. 1	I _(AV)	3.0									Amps
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) @T _L =100°C	I _{FSM}	100.0									Amps
Maximum instantaneous forward voltage @ 3.0A	V _F	0.95				1	1.3		1.7		Volts
Maximum DC reverse current @ T _A =25°C at rated DC blocking voltage @ T _A =100°C	I _R	10.0 500									uA uA
Maximum reverse recovery time (Note 1)	t _m	35									nS
Typical junction capacitance (Note 2)	C _J	50 40						pF			
Typical thermal resistance (Note 3)	R _{eJA} R _{eJL}	47 12									°C/W
Operating junction temperature range	T _J	-55 to +150									°C
Storage temperature range	T _{STG}	-55 to +150									°C

Notes: 1. Reverse Recovery Test Conditions: I_F=0.5A, I_R=1.0A, I_{RR}=0.25A

- 2. Measured at 1 MHz and Applied V_p=4.0 Volts
- 3. Units Mounted on P.C.B. with 0.31 x 0.31" (8.0 x 8.0mm) Copper Pad Areas

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RATINGS AND CHARACTERISTIC CURVES ES3A THRU ES3M

(T₄ = 25°C unless otherwise noted)

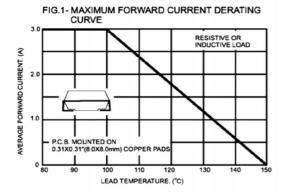


FIG.2- MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

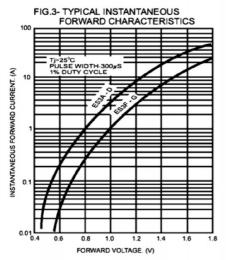
150

8.3ms Single Half Sine Wave (JEDEC Method) at TL=120°C

75

75

NUMBER OF CYCLES AT 60Hz



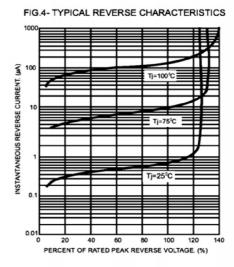


FIG.5- TYPICAL JUNCTION CAPACITANCE

